

Calculations on structural, electronic, and energetic properties

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Overview of the tutorial

- Purpose: This section is to familiarize users with calculating some basic properties of materials. These include relaxing a material to obtain the equilibrium structure at 0 temperature, electronic structure (e.g., density of states and band structure) for a given ionic configuration, and energetic properties of different phases.
- Approaches: SCAN meta-GGA
- Codes: VASP
- Materials: Si

Running SCAN in VASP

INCAR tags:

METAGGA = SCAN

LASPH = .TRUE.

ADDGRID = .TRUE.

POTCAR:

Check if it contains the kinetic energy density of the core electrons:

```
grep kinetic POTCAR
```

Note on Band-structure and DOS calculations

- self-consistent vs. non-self-consistent
- For non-scfconsistent:
 - Need converged charge-density and kinetic energy density
 - Kinetic energy density is not written out after calculation.

four examples

- Si
 - Lattice constant, band structure
 - Phase transition
 - Defect formation energy
- MoS₂
 - Lattice constant, band structure, DOS
 - Non-selfconsistent, “incorrect”

Unusual Mechanical and Electronic Properties of 2D Materials Predicted by Using SCAN

Liping Yu

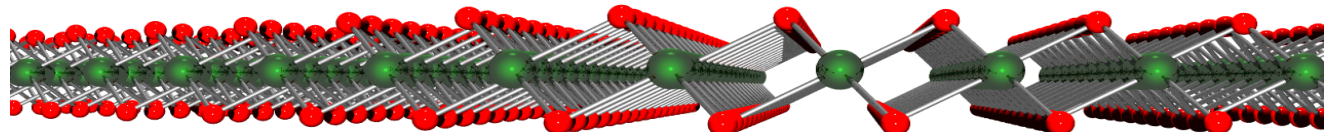
Department of Physics
Temple University

Collaborators:

Qimin Yan, Adrien Ruzsinszky, John Perdew

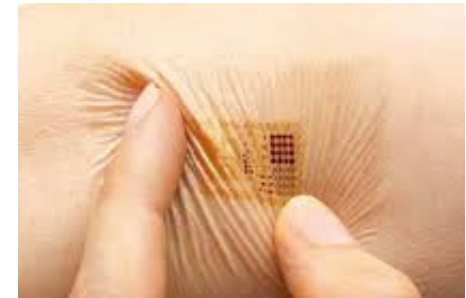
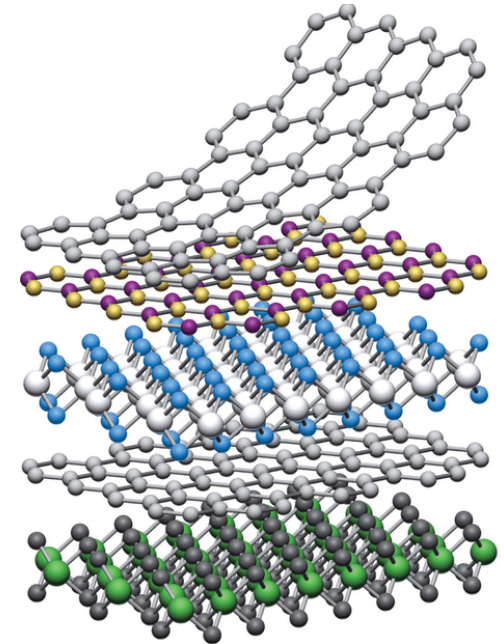


Center for the Computational Design of Functional Layered Materials



Unique Attributes of 2D Materials

- van der Waals interlayer bonding
 - Artificial heterostructures
 - New functionalities
- Atomically thin & highly flexible
 - Flexible and large-area electronics

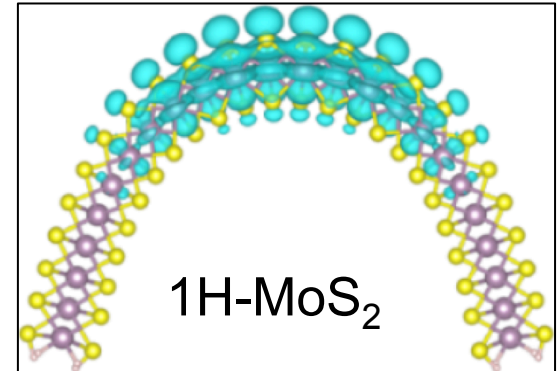


Two examples

- Extraordinary 2D bending effects

- Yu, Ruzsinszky & Perdew

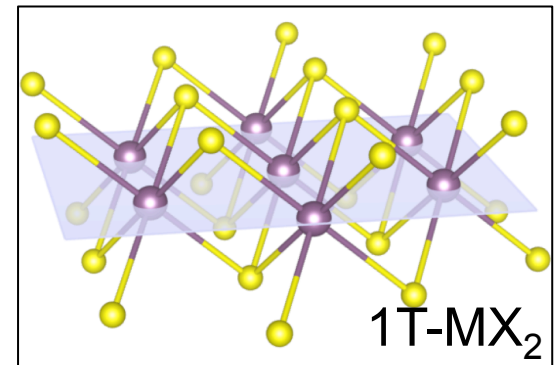
- Nano Letters*, 16, 2444(2016)



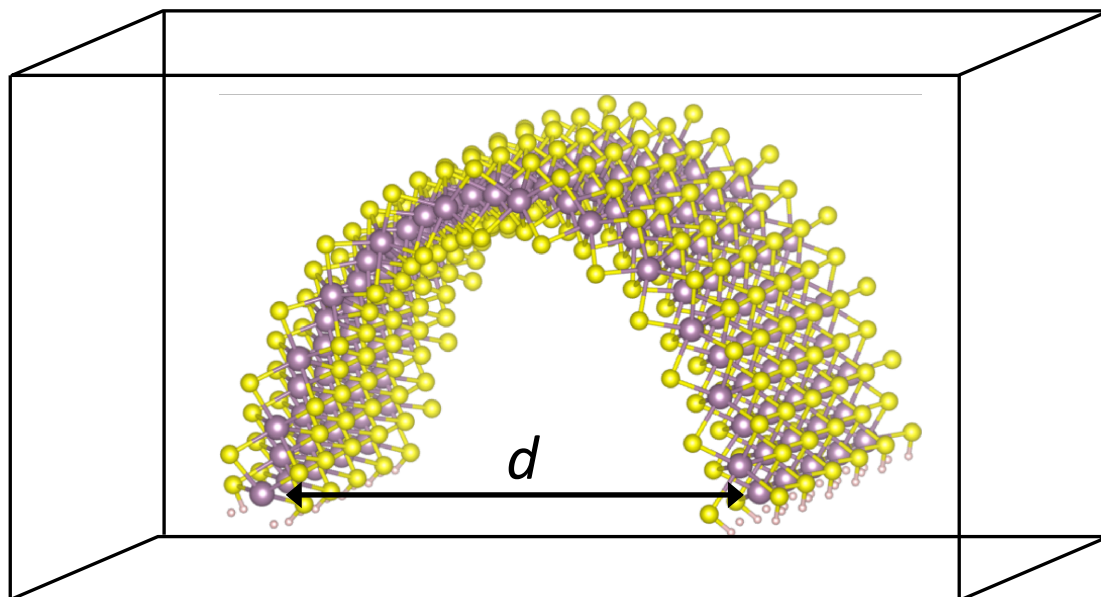
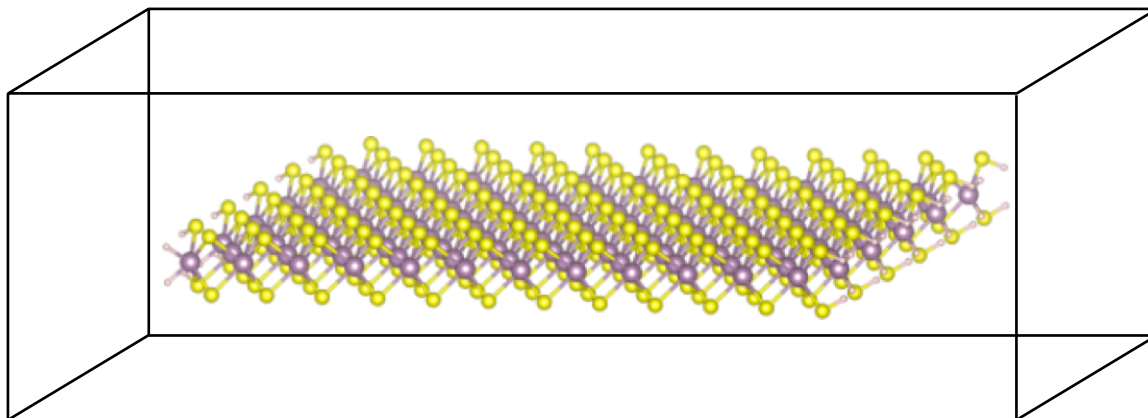
- Counter-intuitive auxetic effects in 1T MX₂

- Yu, Yan & Ruzsinszky,

- Nat. Commun.* 8, 15224 (2017).

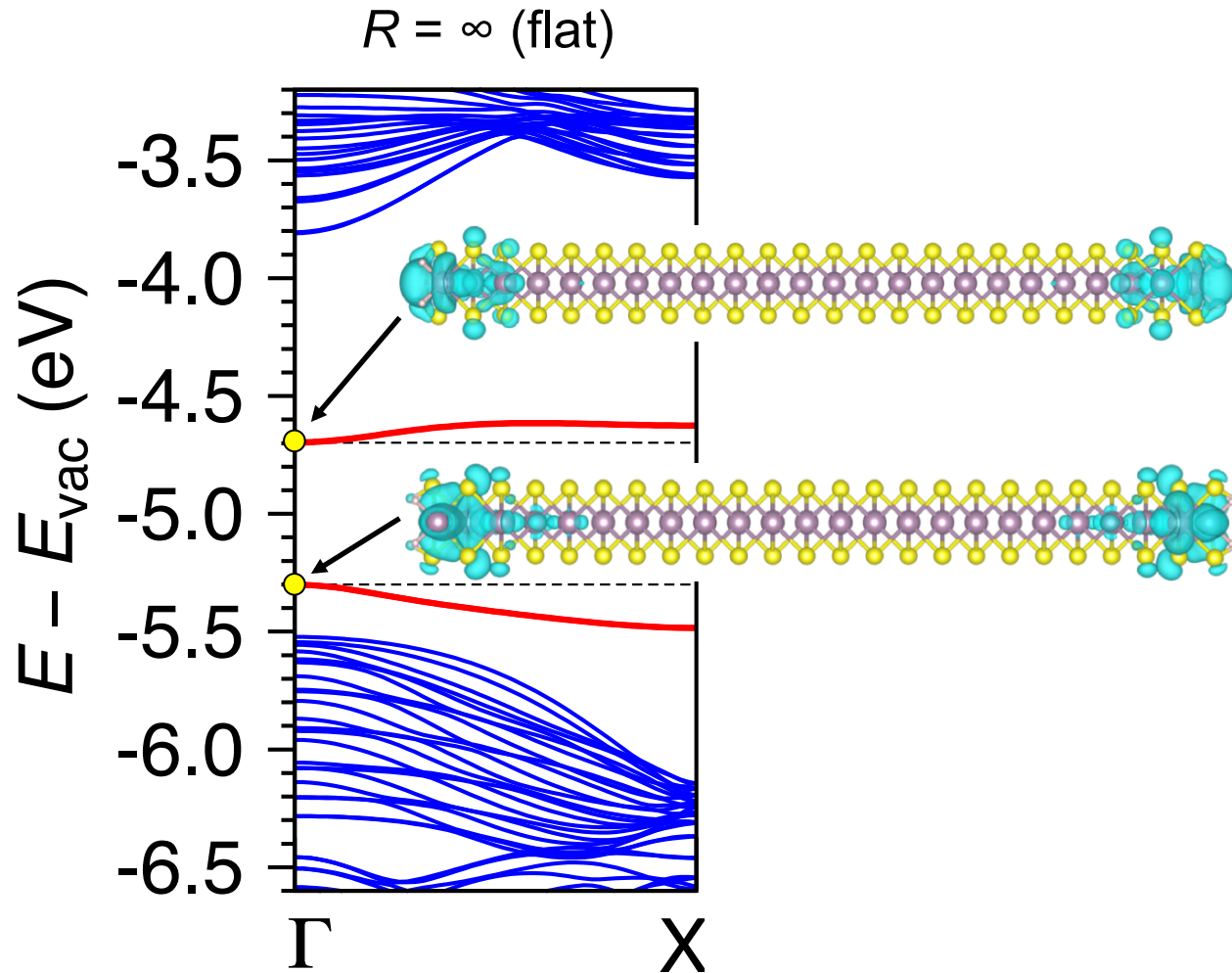


Bending Scheme: Case of MoS₂ Nanoribbon

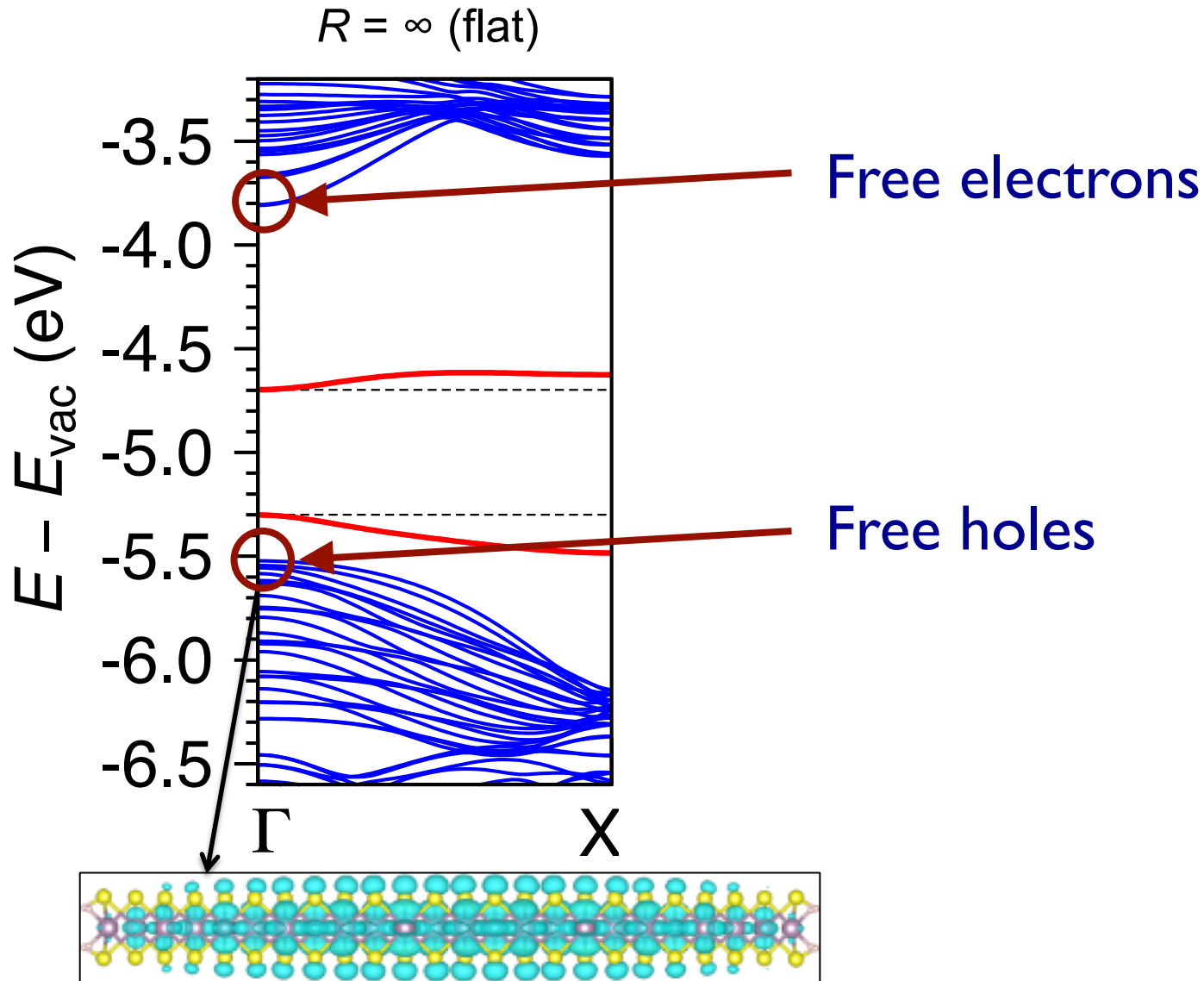


Similar to the set-up
for 2-point bending
stiffness measurement

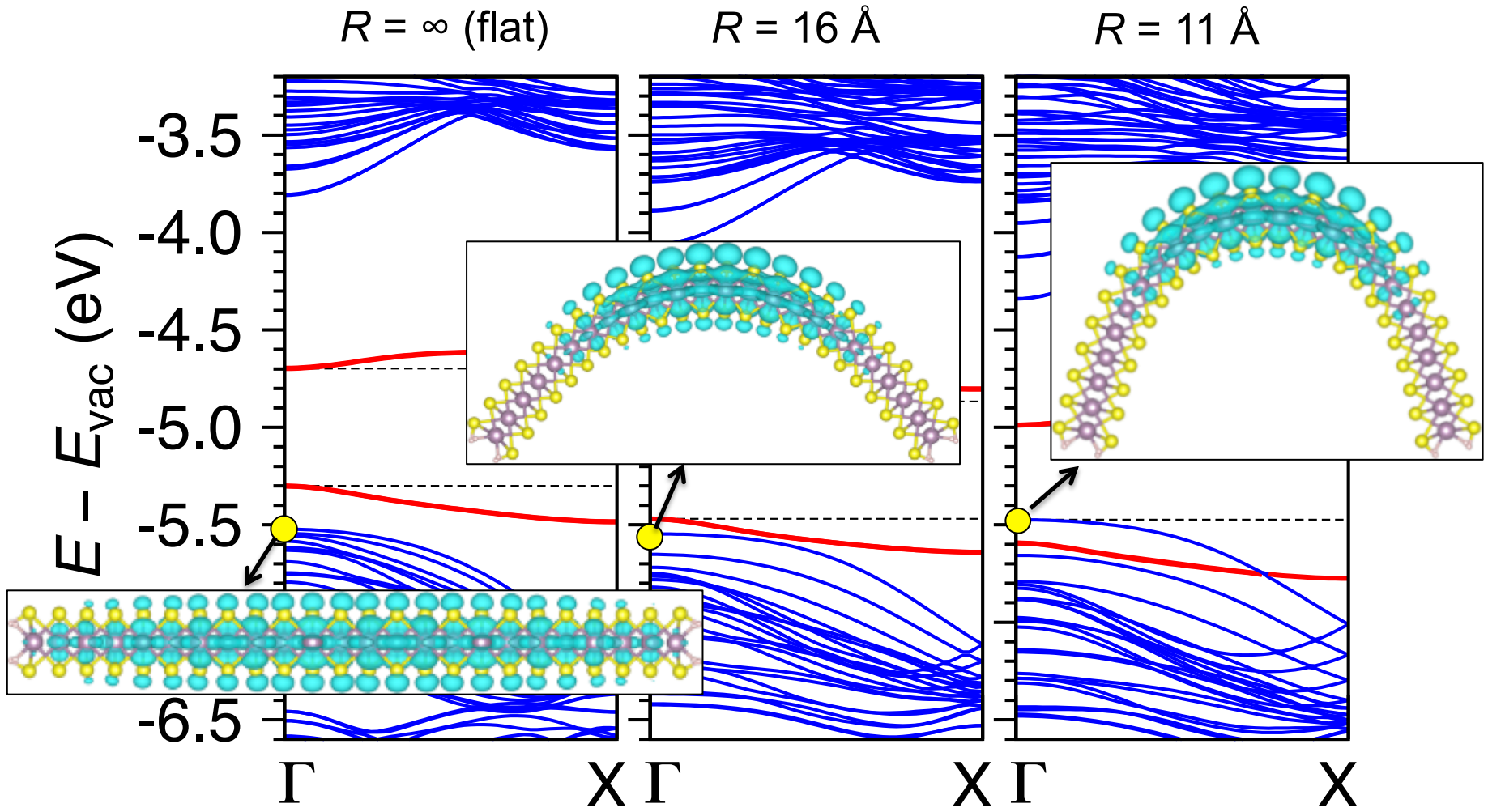
Band Structure of Armchair MoS₂ Nanoribbon



Free Carriers in MoS₂ Semiconductors



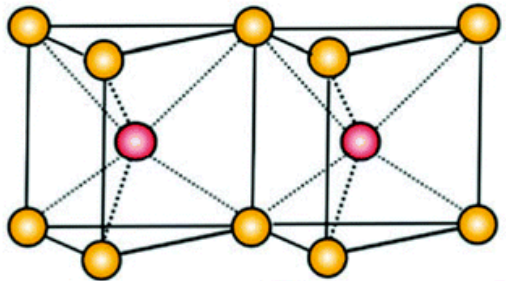
Bending Localizes Hole Carriers in MoS₂



- Bending switches on/off p-type conductivity

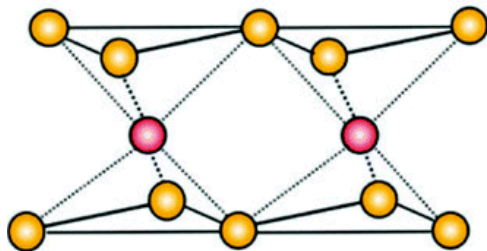
Monolayer MX_2 : 2H vs. 1T

2H
triangular
prismatic



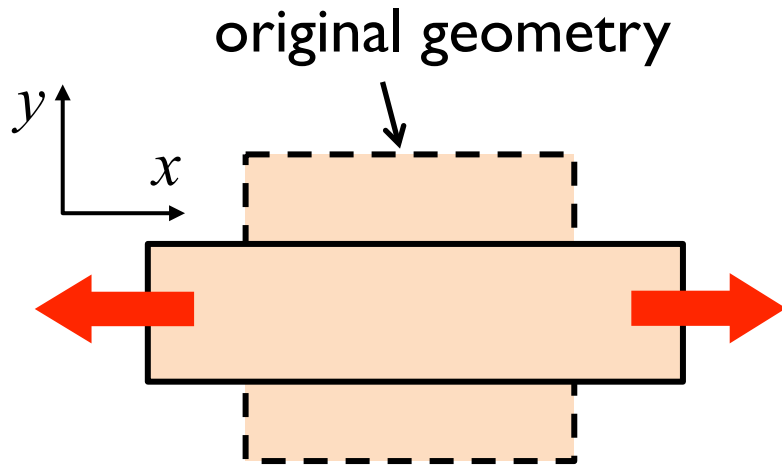
- Mechanical bending can tune conductivity in 2H MX_2 .
- Experimental validation underway

1T
octahedral



- 1T- MX_2 have unusual mechanical response.

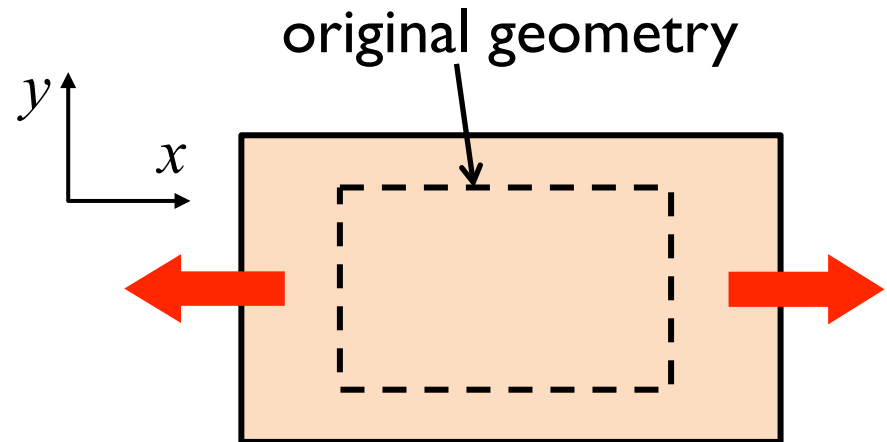
Auxetics: Materials with a Negative Poisson's Ratio



Poisson's
Ratio

$$\nu_{yx} = -\frac{\epsilon_y}{\epsilon_x} > 0$$

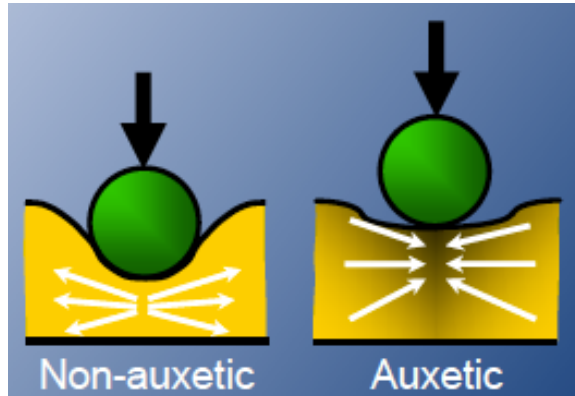
- Non-auxetic



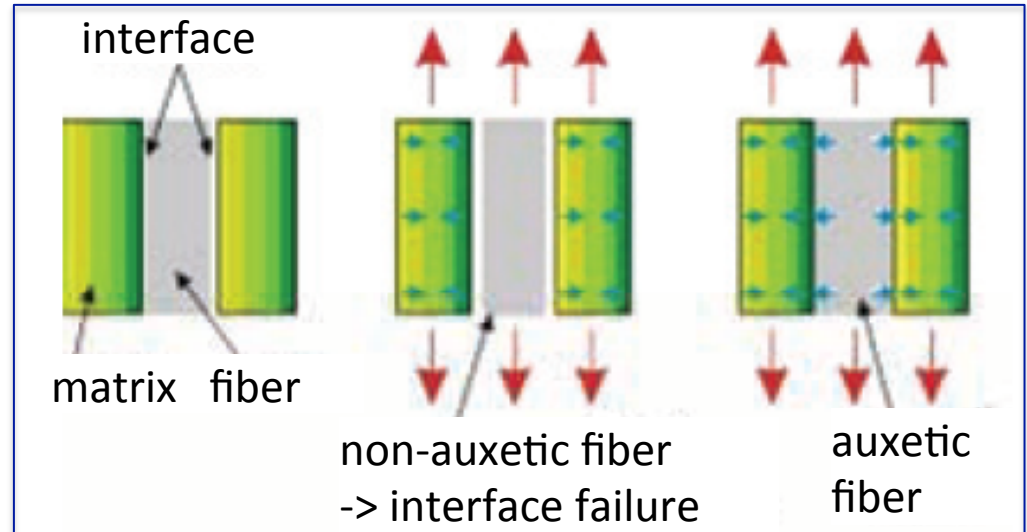
$$\nu_{yx} = -\frac{\epsilon_y}{\epsilon_x} < 0$$

- Auxetic
- counter-intuitive
- Unusual

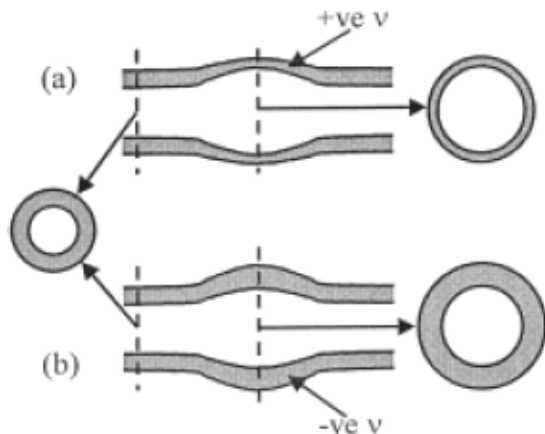
Potential Applications



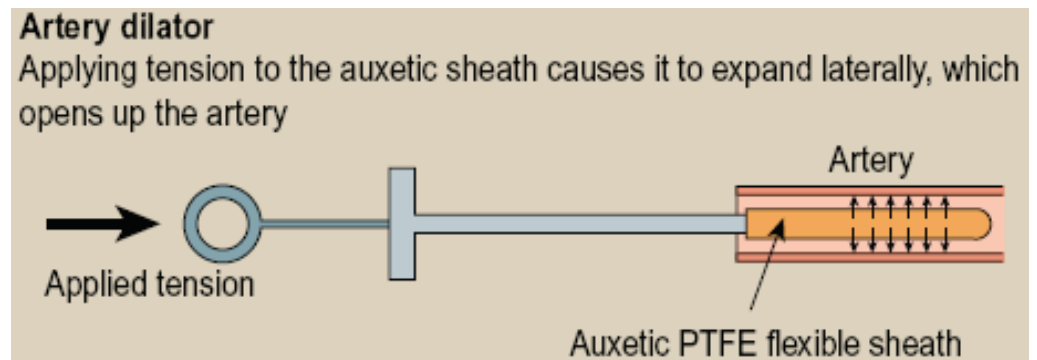
Bulletproof Vest & Armor Enhancement



Auxetic Fiber Reinforced Composites

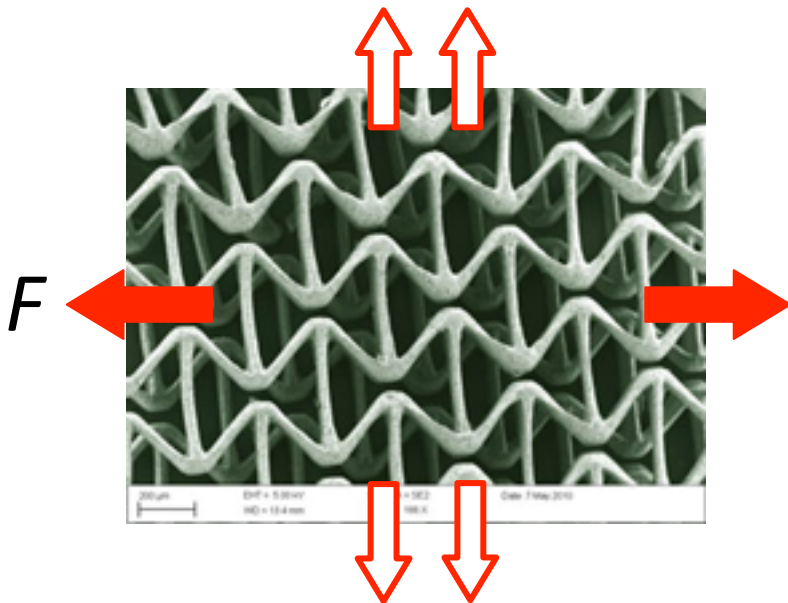


Artificial Blood Vessels



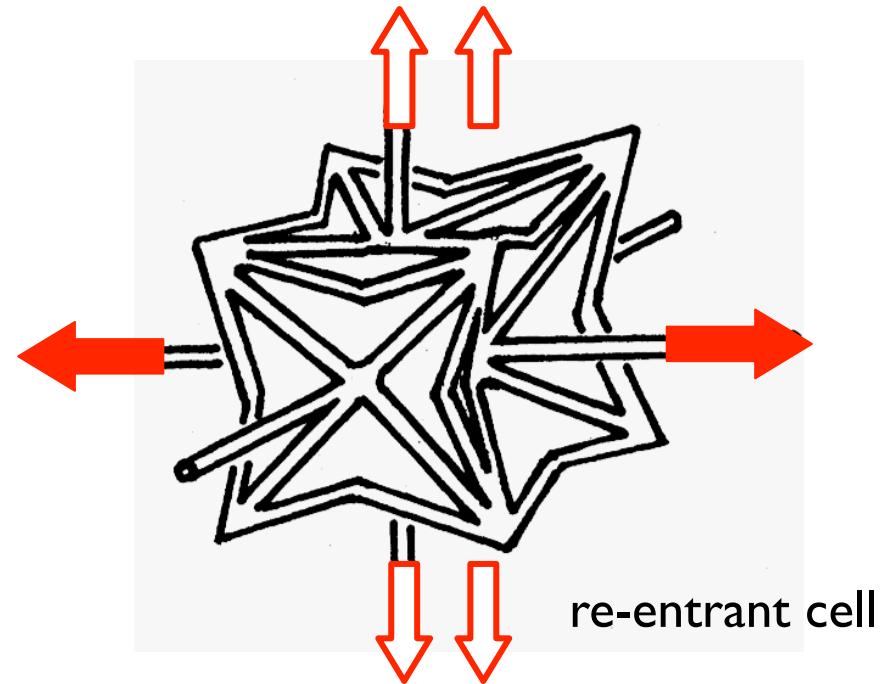
Artery Dilator

Common Structural Mechanisms



Polymer constructs

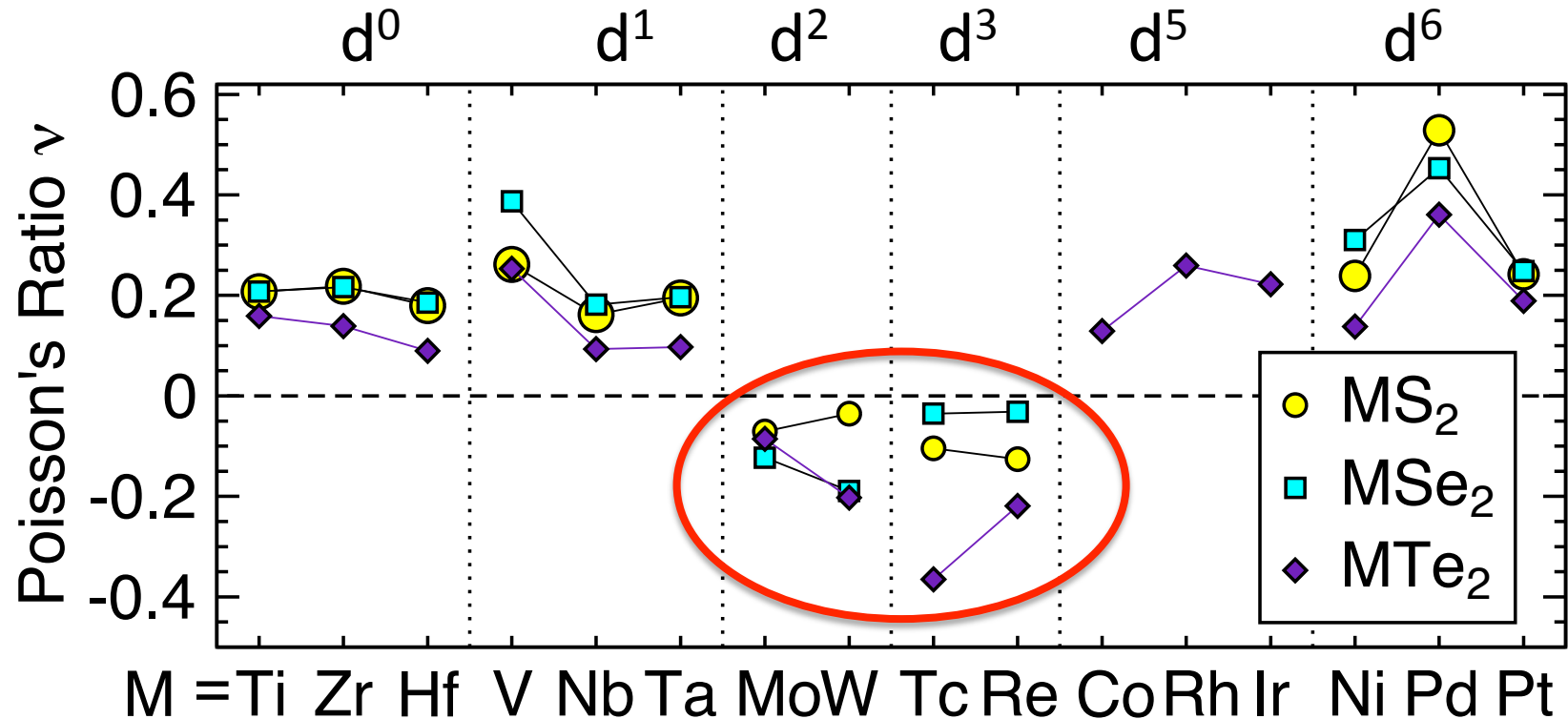
Adv. Funct. Mater, 21, 2712(2011)



Lakers, Science 235, 1038(1987)

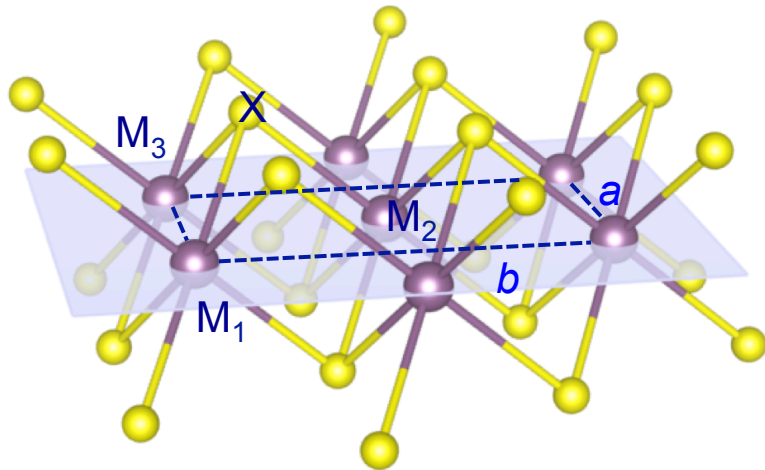
- NPR is often considered as a purely geometric property.

This work finds a new type of auxetic materials: IT-MX₂

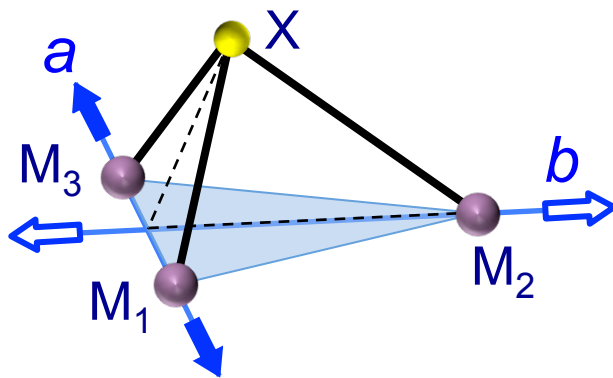


- Only d^2 and d^3 MX₂ compounds exhibit an intrinsic in-plane NPR.
- NPR is not a purely geometric property.

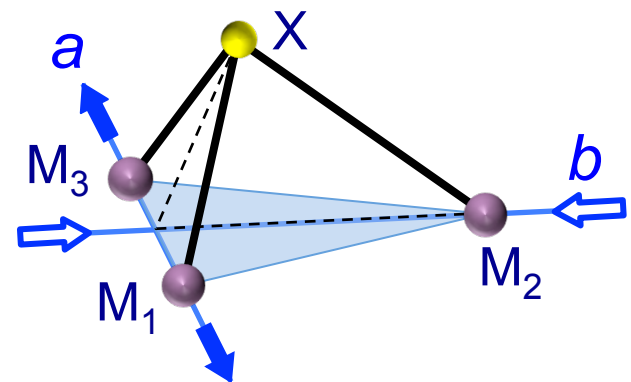
Structural Deformation Mechanism



Basic Building Unit :
X-M₁M₂M₃ triangular pyramid



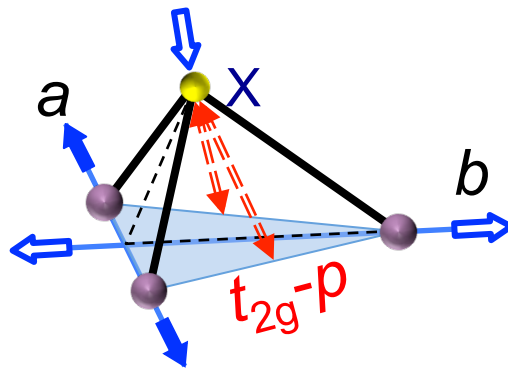
auxetic



non-auxetic

Electronic Origin: t_{2g} -p Interaction

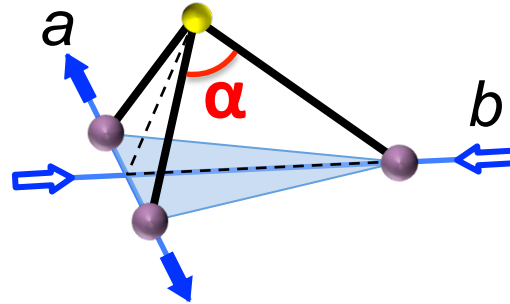
d^2-d^3
auxetic



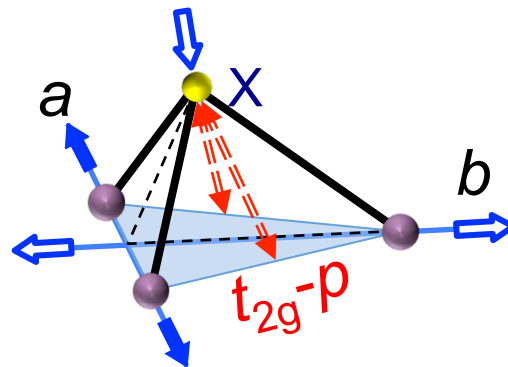
- Strong t_{2g} -p orbital interaction attracts X atom toward the basal plane.

Electronic Origin: t_{2g} -p Interaction

d^0 - d^1
non-auxetic



d^2 - d^3
auxetic

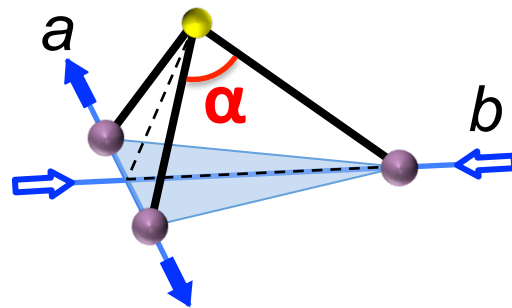


- Weak or marginal t_{2g} -p orbital interaction

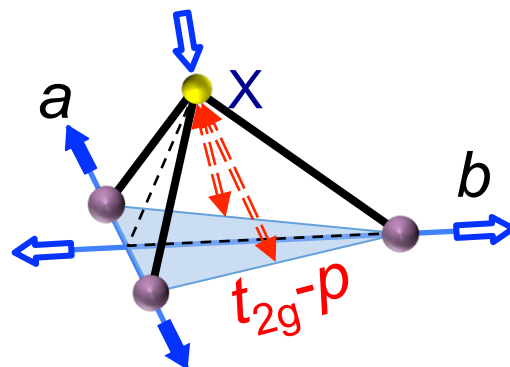
- Strong t_{2g} -p orbital interaction attracts X atom toward the basal plane.

Electronic Origin: t_{2g} -p Interaction

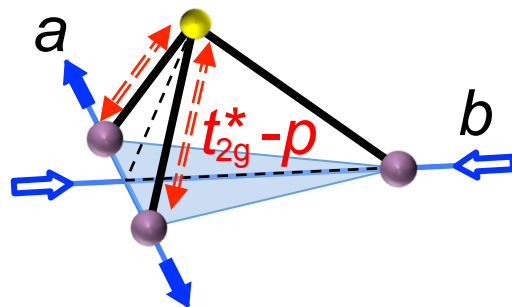
d^0 - d^1
non-auxetic



d^2 - d^3
auxetic



d^5 - d^6
non-auxetic

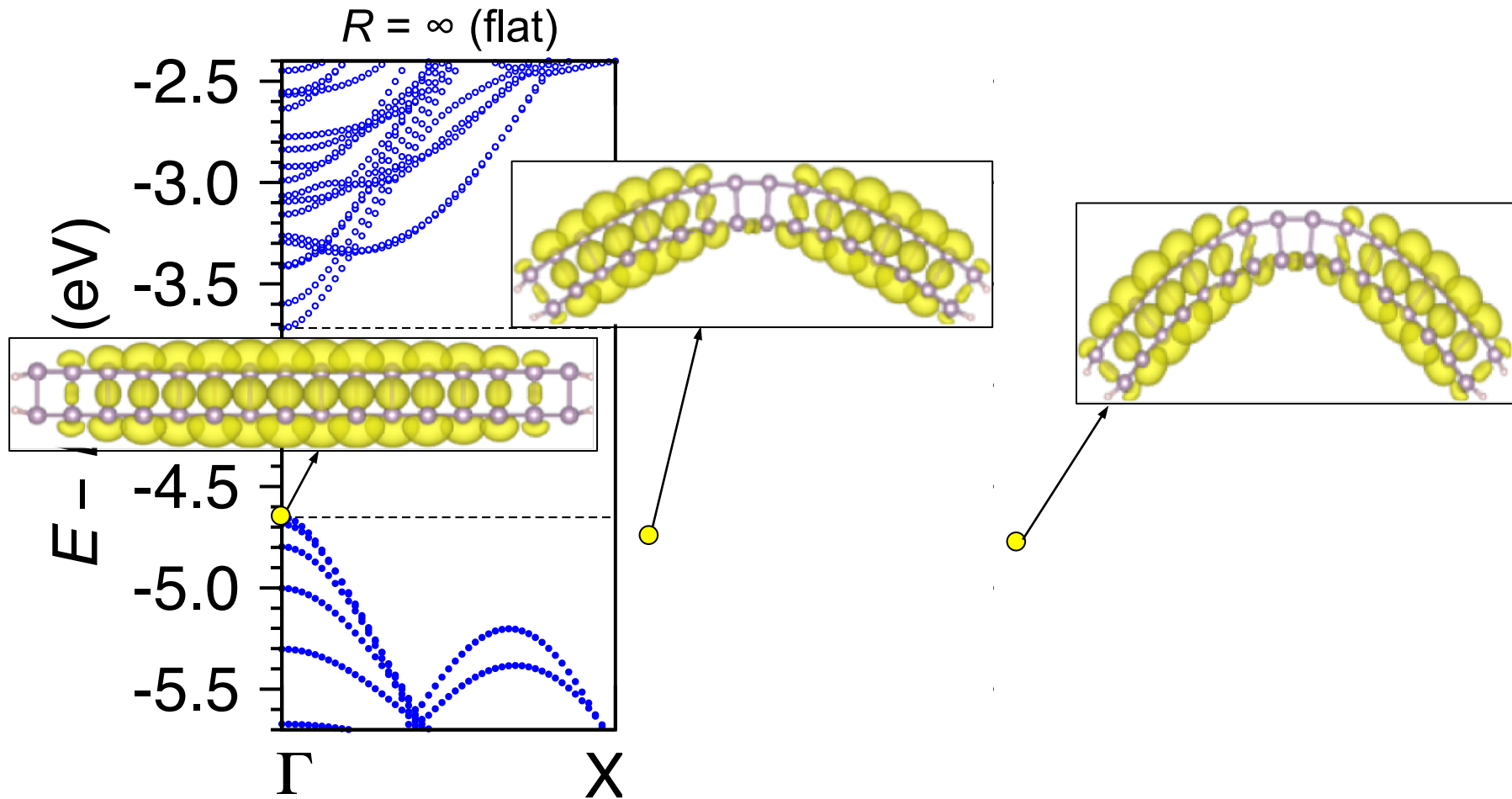


- Weak or marginal t_{2g} -p orbital interaction
- Strong t_{2g} -p orbital interaction attracts X atom toward the basal plane.
- Strong t_{2g}^* -p orbital interaction lies along the bond direction.

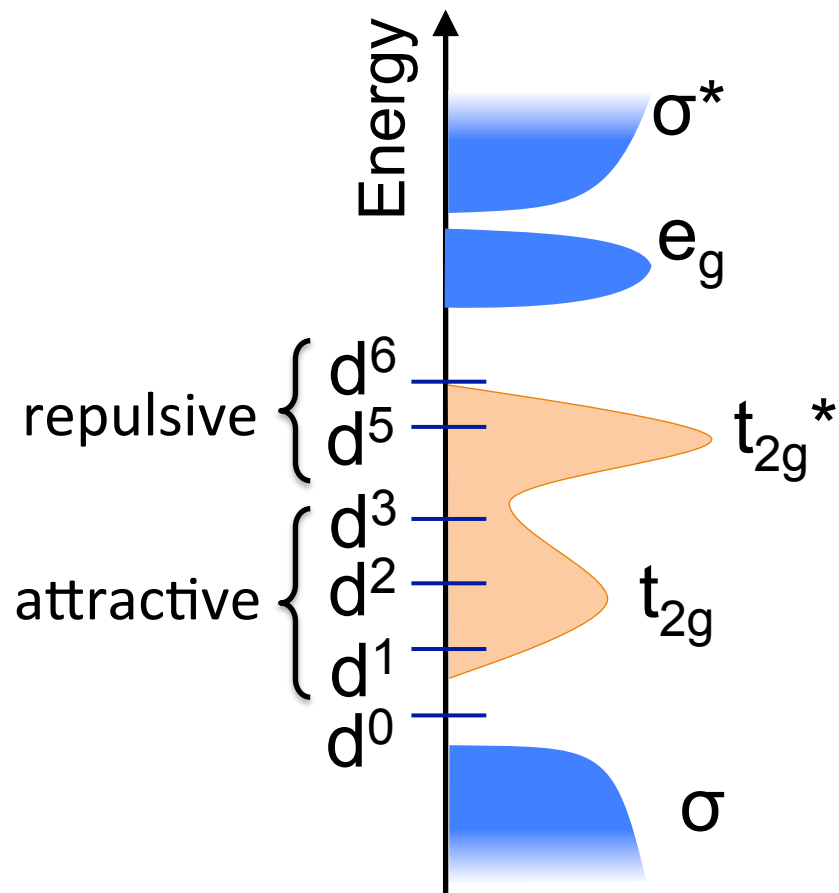
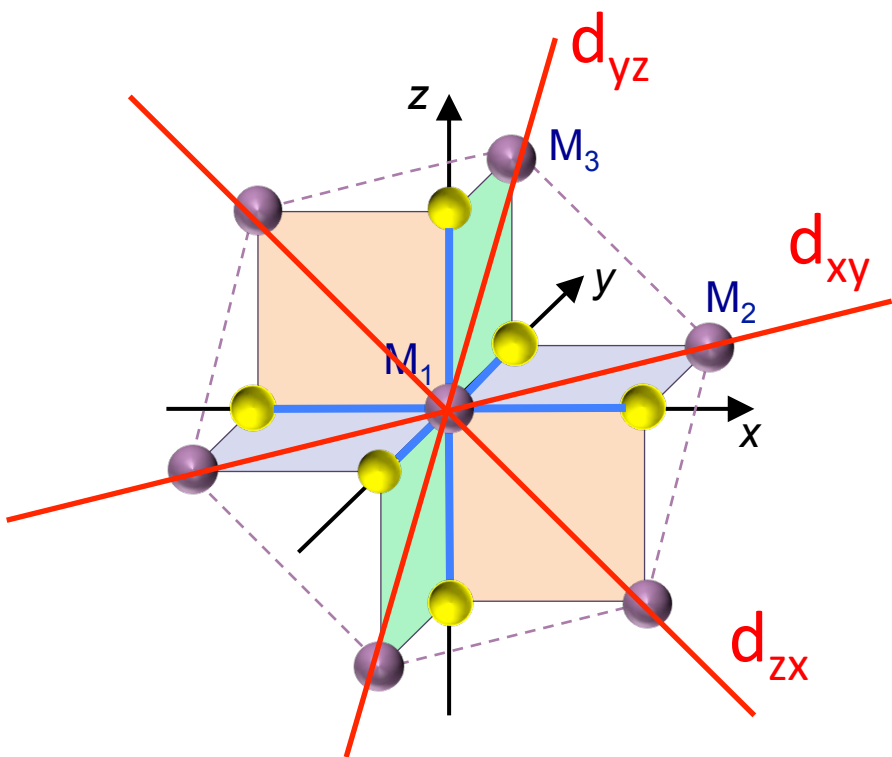
Conclusions

- Mechanical bending can be used to tune charge localization (hence conductivity) in MoS₂ and phosphorene nanoribbons.
- d²-d³ IT-MX₂: a new type of auxetic 2D materials

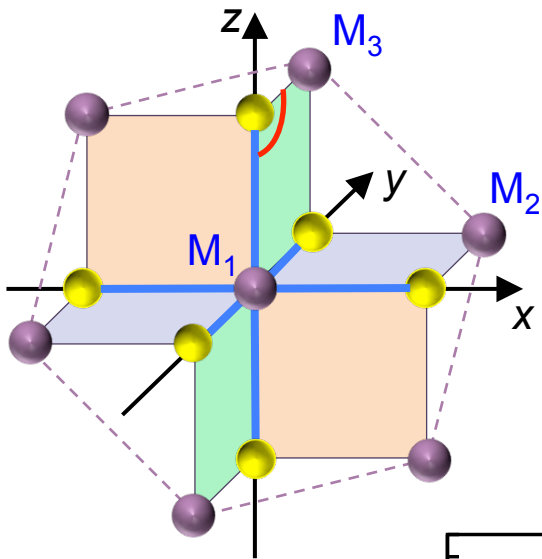
Bending Localizes Hole Carriers in Phosphorene



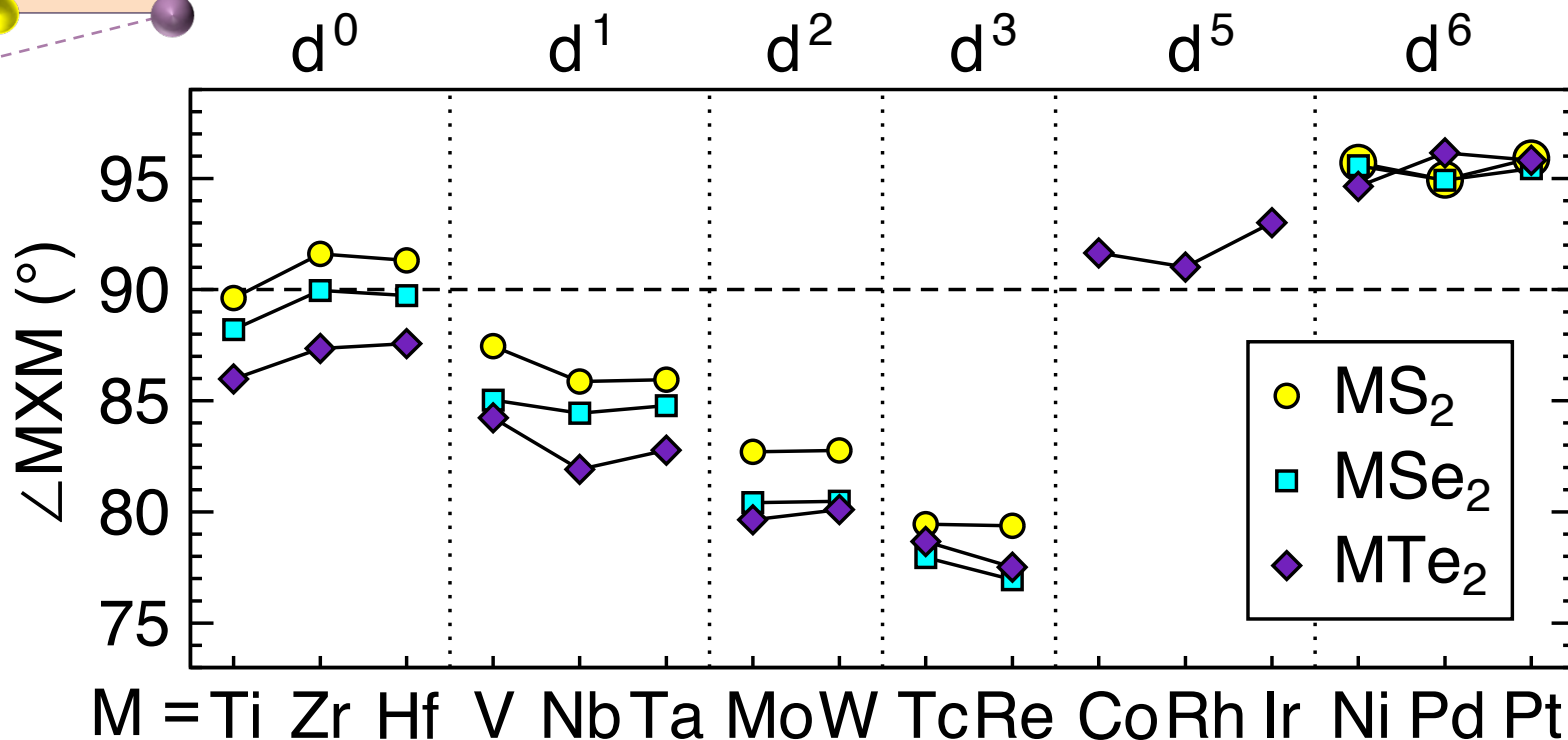
Intermetal t_{2g} -orbital Interaction



Evidence of Intermetal t_{2g} Coupling



- M-X-M bond angles depend on d-electron count



Intermetal t_{2g} - $p(X)$ Interaction

